

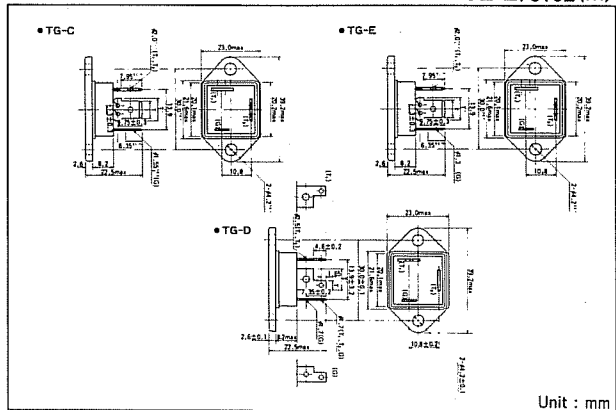
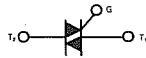
TRIAC (ISOLATED TYPE)

TG35C/E/D

UL:E76102(M)

TG35C/E/D are isolated mould triac suitable for wide range of applications like copier, Microwave oven, solid state switch, motor control, light control and heater control.

- I_T (RMS) 35A
- High Surge Capability 330A
- Isolated Mounting (AC2500V)
- Tab Terminals



Unit : mm

Maximum Ratings

C, E and D type have same electrical characteristics

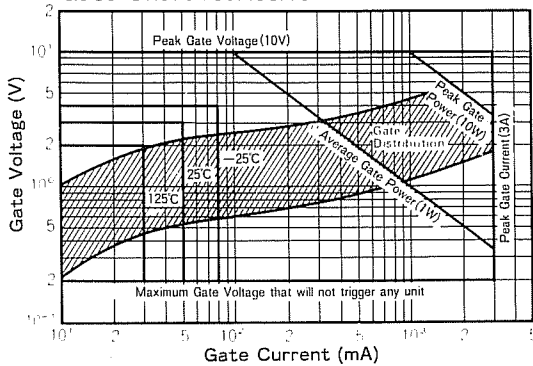
Symbol	Item	TG35C40	TG35C60	Unit
V_{DRM}	Repetitive Peak off-State Voltage	400	600	V

Symbol	Item	Conditions	Ratings	Unit
I_T (RMS)	R.M.S On-State Current	$T_c = 58^\circ\text{C}$	35	A
I_{TSM}	Surge On-State Current	One cycle, 50/60Hz, peak, non-repetitive	300/330	A
I^2t	I^2t	Value for one cycle of surge current	450	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	$I_G = 100\text{mA}$, $T_j = 25^\circ\text{C}$, $V_D = \frac{1}{2} V_{DRM}$, $di_G/dt = 1\text{A}/\mu\text{s}$	50	$\text{A}/\mu\text{s}$
T_j	Operating Junction Temperature		$-25 \sim +125$	$^\circ\text{C}$
T_{stg}	Storage Temperature		$-40 \sim +125$	$^\circ\text{C}$
V_{iso}	Isolation Breakdown Voltage(R.M.S)	A.C. 1minute	2500	V
	Mounting Torque	Recommended Value 10 $\text{kgf}\cdot\text{cm}$	12	$\text{kgf}\cdot\text{cm}$
	Mass	Excluding bolt, nut and wrapping material	23	g

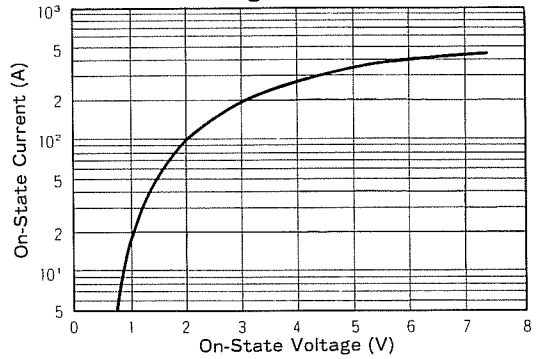
Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j = 125^\circ\text{C}$	5	mA
V_{TM}	Peak On-State Voltage, max.	$(\sqrt{2} \times I_T(\text{RMS}))$ $T_j = 25^\circ\text{C}$ Inst. measurement	1.4	V
I_{GT1}^+	Gate Trigger Current, max.	$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	50	mA
I_{GT1}^-		$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	50	
I_{GT3}^+			—	
I_{GT3}^-		$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	50	
V_{GT1}^+	Gate Trigger Voltage, max.	$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	3	V
V_{GT1}^-		$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	3	
V_{GT3}^+			—	
V_{GT3}^-		$T_j = 25^\circ\text{C}$, $I_T = 1\text{A}$, $V_D = 6\text{V}$	3	
V_{GD}	Non-Trigger Gate Voltage, min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{1}{2} V_{DRM}$	0.2	V
t_{gt}	Turn On Time, max	$I_T(\text{RMS})$, $I_G = 100\text{mA}$, $V_D = \frac{1}{2} V_{DRM}$, $T_j = 25^\circ\text{C}$ $di_G/dt = 1\text{A}/\mu\text{s}$	10	μs
dv/dt	Critical Rate of Rise of On-State Voltage, min.	$T_j = 125^\circ\text{C}$, $V_D = \frac{2}{3} V_{DRM}$, Exponential wave.	20	$\text{V}/\mu\text{s}$
$(dv/dt)_c$	Critical Rate of Rise off-State Voltage at commutation, min	$T_j = 125^\circ\text{C}$, $(di/dt)_c = 15\text{A}/\text{ms}$, $V_D = \frac{2}{3} V_{DRM}$	5	$\text{V}/\mu\text{s}$
I_H	Holding Current, typ.	$T_j = 25^\circ\text{C}$	30	mA
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to case	1.5	$^\circ\text{C}/\text{W}$

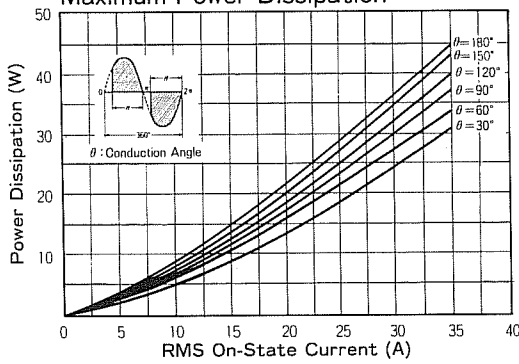
Gate Characteristics



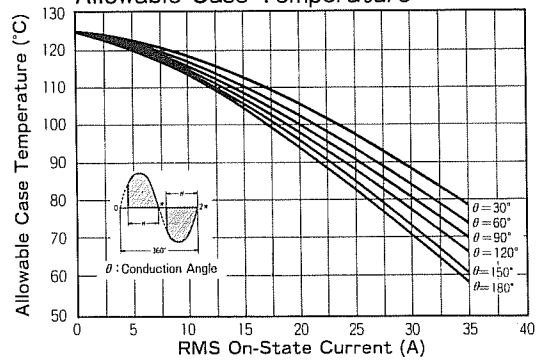
On-state Voltage



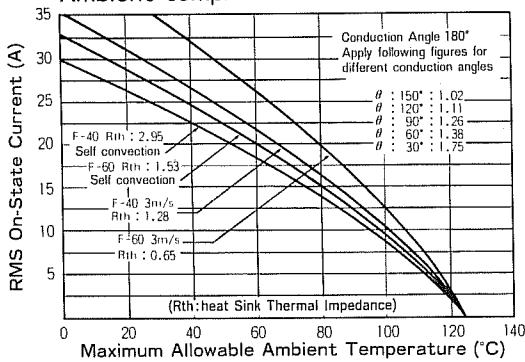
On state Current vs. Maximum Power Dissipation



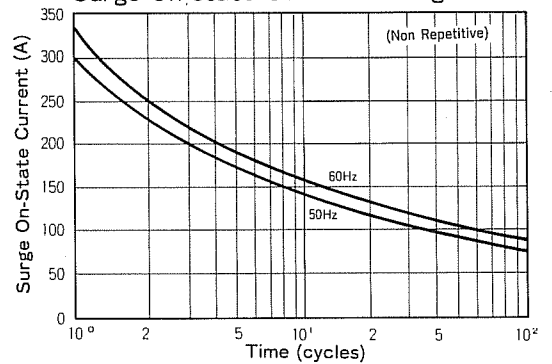
On state Current vs. Allowable Case Temperature



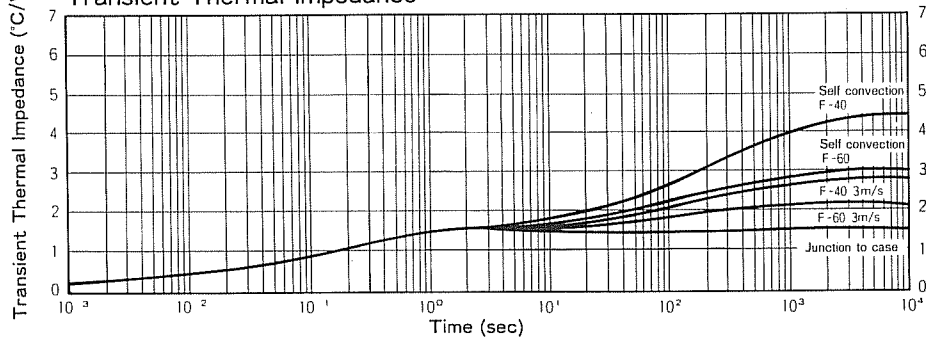
Ambient temp. vs. RMS On state Current



Surge On state Current Rating



Transient Thermal Impedance



TRIAC